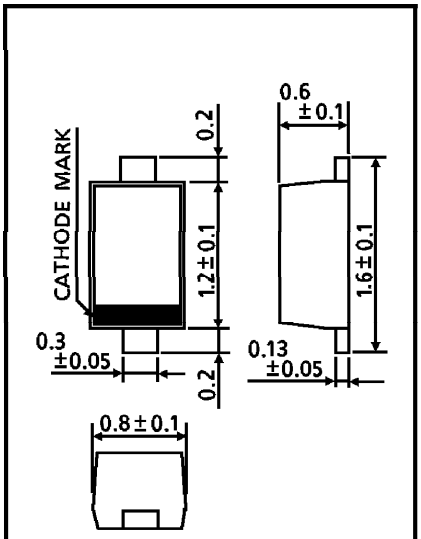
TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

1SV325

TCXO / VCO

Unit in mm

- High Capacitance Ratio : $C_{1V} / C_{4V} = 4.3$ (Typ.)
- Low Series Resistance : $r_s = 0.4\ \Omega$ (Typ.)
- Useful for Small Size Tuner.



ESC	
JEDEC	—
EIAJ	—
TOSHIBA	1-1G1A

Weight : 0.0014 g

MAXIMUM RATINGS (Ta = 25°C)

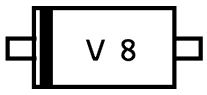
CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	10	V
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V_R	$I_R = 1\ \mu A$	10	—	—	V
Reverse Current	I_R	$V_R = 10$ V	—	—	3	nA
Capacitance	C_{1V}	$V_R = 1$ V, f = 1 MHz	44	—	49.5	pF
Capacitance	C_{4V}	$V_R = 4$ V, f = 1 MHz	9.2	—	12	pF
Capacitance Ratio	C_{1V} / C_{4V}	—	4	4.3	—	—
Series Resistance	r_s	$V_R = 4$ V, f = 100 MHz	—	0.4	0.8	Ω

* Signal level when capacitance is measured : Vsig = 500 mV_{rms}

MARKING



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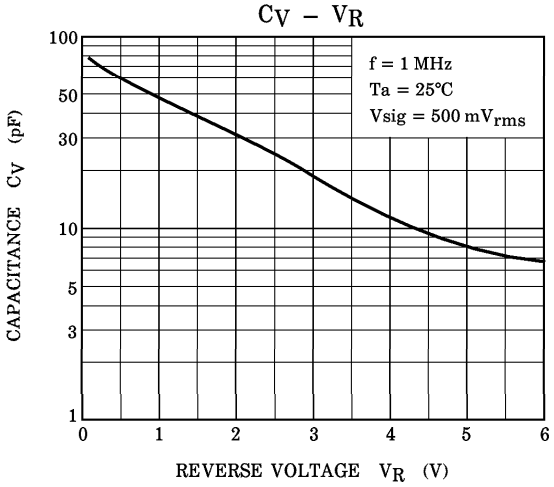
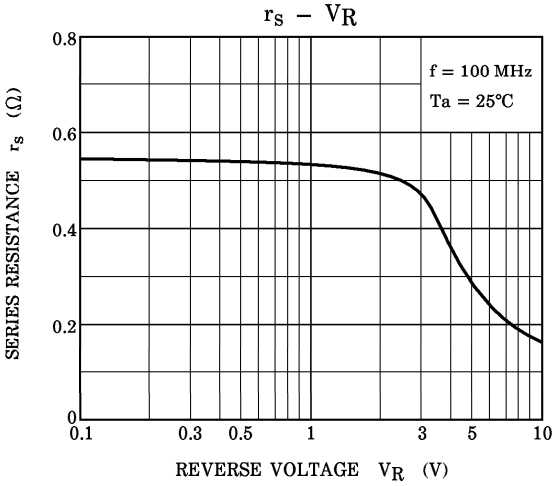

$C_V - V_R$
f = 1 MHz
Ta = 25°C
Vsig = 500 mV_{rms}
CAPACITANCE C_V (pF)
100
50
30
10
5
3
1
0
1
2
3
4
5
6
REVERSE VOLTAGE V_R (V)


$r_s - V_R$
f = 100 MHz
Ta = 25°C
SERIES RESISTANCE r_s (Ω)
0.8
0.6
0.4
0.2
0
0.1
0.3
0.5
1
3
5
10
REVERSE VOLTAGE V_R (V)